

Quyen Leung

308-0545

CP4-5A07

08/808, 318

Quyen

Please Contact darcy bates- 306-5419
if you need the full text of any of these.

Karen Lehman

306-5783

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?show files;ds;t 7/3,k/all
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Set	Items	Description
S1	291	AU="MORITA E" OR AU="MORITA ETSUO"
S2	2103	AU="KAWAI H"
S3	18	AU="KAWAI HIROJI"
S4	0	S1 AND SAPPHIRE?
S5	23	S1 AND (SEMICONDUCTOR? OR SEMI() CONDUCT?)
S6	5	(S2 OR S3) AND SAPPHIRE?
S7	19	RD S5 (unique items)

>>>KWIC option is not available in file(s): 14, 77

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7/3,K/1      (Item 1 from file: 144)
DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

```

13772732 PASCAL No.: 98-0485739

Room-temperature pulsed operation of a GaInN multiple-quantum-well laser
diode with optimized well number

Nitride **semiconductors** 1997

NAKAMURA F; KOBAYASHI T; ASATSUMA T; FUNATO K; YANASHIMA K; HASHIMOTO S;
NAGANUMA K; TOMIOKA S; MIYAJIMA T; **MORITA E**; KAWAI H; IKEDA M
HIRAMATSU K, ed; KISHINO K, ed; NAKAMURA S, ed; AMANO H, ed
Research Center, Sony Corporation, 174 Fujitsuka-cho, Hodogaya-ku,

Yokohama 240, Japan

Mie University, Japan; Sophia University, Japan; Nichia Chemical Industries, Japan; Meijo University, Japan

The Japan Society of Applied Physics, Japan.

ICNS'97 International Conference on Nitride Semiconductors, 2 (Tokushima JPN) 1997-10-27

Journal: Journal of crystal growth, 1998, 189-90 841-845

Language: English

Copyright (c) 1998 INIST-CNRS. All rights reserved.

Nitride **semiconductors 1997**

...T; ASATSUMA T; FUNATO K; YANASHIMA K; HASHIMOTO S; NAGANUMA K; TOMIOKA S; MIYAJIMA T; **MORITA E**; KAWAI H; IKEDA M

English Descriptors: Injection laser; **Semiconductor** laser; Multiple quantum well; Room temperature; III-V compound; Gallium Nitrides; Binary compound; Indium Nitrides...

Spanish Descriptors: Laser inyeccion; Laser **semiconductor**; Pozo cuantico multiple; Temperatura ambiente; Compuesto III-V; Galio Nitruro; Compuesto binario; Indio Nitruro; Compuesto...

7/3,K/2 (Item 2 from file: 144)

DIALOG(R)File 144:Pascal

(c) 2000 INIST/CNRS. All rts. reserv.

13393233 PASCAL No.: 97-0578628

Surface morphology changes in ZnSe-related II-VI epitaxial films grown by molecular beam epitaxy

TOMIYA S; MINATOYA R; TSUKAMOTO H; ITOH S; NAKANO K; **MORITA E**; ISHIBASHI A

Sony Corporation Research Center, 174, Fujitsuka-cho, Hodogaya-ku, Yokohama 240, Japan

Journal: Journal of applied physics, 1997-09-15, 82 (6) 2938-2943

Language: English

Copyright (c) 1997 American Institute of Physics. All rights reserved.

TOMIYA S; MINATOYA R; TSUKAMOTO H; ITOH S; NAKANO K; **MORITA E**; ISHIBASHI A

English Descriptors: Experimental study; Zinc compounds; II-VI **semiconductors**; **Semiconductor** epitaxial layers; Molecular beam epitaxy; **Semiconductor** growth; Surface structure; Surface reconstruction; Atomic force microscopy; TEM

7/3,K/3 (Item 3 from file: 144)

DIALOG(R)File 144:Pascal

(c) 2000 INIST/CNRS. All rts. reserv.

10906601 PASCAL No.: 93-0415965

Field ion-scanning tunneling microscope equipped with molecular beam epitaxy and its application to study **semiconductor surface structure Nanoscale science**

MIWA S; HAGA Y; **MORITA E**; ARAKAWA S; HASHIZUME T; SAKURAI T AONO M, ed; HASHIZUME T, ed; KAWAI T, ed; ONO M, ed; SAKAI A, ed; SAKURAI T, ed

Sony Corp. Research Center, Hodogaya, Yokohama 240, Japan

Journal: Japanese journal of applied physics, 1993, 32 (3B p.1) 1508-1510

Language: English

Field ion-scanning tunneling microscope equipped with molecular beam

epitaxy and its application to study **semiconductor surface structure**
MIWA S; HAGA Y; **MORITA E**; ARAKAWA S; HASHIZUME T; SAKURAI T
... cells and reflection high energy electron diffraction (RHEED). This
system allows us to observe compound **semiconductor** surfaces such as
GaAs while keeping their surfaces clean. In this paper, this system was...

English Descriptors: Experimental study; Growth from vapor; Molecular beam
condensation; Epitaxy; Thin film; **Semiconductor** materials; Surface
structure; Inorganic compound; Annealing; Gallium Arsenides; Silicon;
Crystal face; Scanning tunneling microscopy; Field...

Spanish Descriptors: Estudio experimental; Metodo fase vapor; Condensacion
haz molecular; Epitaxia; Capa fina; **Semiconductor** (material);
Estructura superficie; Compuesto inorganico; Recocido; Galio Arseniuro;
Silicio; Cara cristal; Microscopia tunel barrido; Microscopia...

7/3,K/4 (Item 4 from file: 144)

DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

10334602 PASCAL No.: 92-0538061
**Quantitative analysis of surface contaminations on Si wafers by total
reflection X-ray fluorescence**
KONDO H; RYUTA J; **MORITA E**; YOSHIMI T; SHIMANUKI Y
Mitsubishi Materials Corp., cent. res. inst., Saitama 330, Japan
Journal: Japanese journal of applied physics, 1992, 31 (1A-B p.2)
L11-L13
Language: English

KONDO H; RYUTA J; **MORITA E**; YOSHIMI T; SHIMANUKI Y

...
...
English Descriptors: study; Impurity; Surface; Integrated intensity;
Impurity density; Scanning electron microscopy; X ray fluorescence; Total
reflection; **Semiconductor** materials; Pastille; Silicon-SUB;
Transition metal-SEC; Iron; Nickel; Copper

Spanish Descriptors: Estudio experimental; Impureza; Superficie; Intensidad
integrada; Concentracion impureza; Microscopia electronica barrido;
Fluorescencia RX; Reflexion total; **Semiconductor** (material); Pastilla;
Silicio-SUB; Metal transicion-SEC; Hierro; Niquel; Cobre

7/3,K/5 (Item 5 from file: 144)

DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

10131473 PASCAL No.: 92-0337226
**Effect of crystal pulling rate on formation of crystal-originated
particles on Si wafers**
RYUTA J; **MORITA E**; TANAKA T; SHIMANUKI Y
Mitsubishi Materials Corp., cent. res. inst., Omiya Saitama 330, Japan
Journal: Japanese journal of applied physics, 1992, 31 (3B p.2)
L293-L295
Language: English

RYUTA J; **MORITA E**; TANAKA T; SHIMANUKI Y

English Descriptors: Experimental study; Crystal defect; Surface;
Semiconductor materials; Silicon; Wafer; Growth from melt; Operating
conditions; Distribution; Particle size; Surface treatment; Chemical
etching...

Spanish Descriptors: Estudio experimental; Defecto cristalino; Superficie;
Semiconductor (material); Silicio; Pastilla electronica; Metodo fase
fundida; Condicion operatoria; Distribucion; Dimension particula;

• Tratamiento superficie; Ataque...

7/3,K/6 (Item 6 from file: 144)
DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

08823381 PASCAL No.: 89-0372786

Transmission electron microscopic study of the ordered structure in GaInP/GaAs epitaxially grown by metalorganic chemical vapor deposition
MORITA E; IKEDA M; KUMAGAI O; KANEKO K
Sony corp., Hodogaya-ku Yokohama 240, Japan
Journal: Applied Physics Letters, 1988, 53 (22) 2164-2166
Language: English

MORITA E; IKEDA M; KUMAGAI O; KANEKO K

English Descriptors: Experimental study; Inorganic compound;
Semiconductor materials; Electron diffraction; Transmission electron microscopy; Epitaxy; Organometallic compound; Crystal growth; Chemical vapor deposition; Heteroepitaxy...

Spanish Descriptors: Estudio experimental; Compuesto inorganico;
Semiconductor (material); Difraccion electronica; Microscopia electronica transmision; Epitaxia; Compuesto organometalico; Crecimiento cristalino; Deposito quimico fase vapor...

7/3,K/7 (Item 7 from file: 144)
DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

08734676 PASCAL No.: 89-0283932
GaInP/AlGaInP double-heterostructure laser grown on a (111)B-oriented GaAs substrate by metalorganic chemical vapour deposition
IKEDA M; **MORITA E**; TODA A; YAMAMOTO T; KANEKO K
Sony corp., Hodogaya-ku Yokohama 240, Japan
Journal: Electronics Letters, 1988, 24 (17) 1094-1095
Language: English

IKEDA M; **MORITA E**; TODA A; YAMAMOTO T; KANEKO K

English Descriptors: **Semiconductor** laser; Double heterojunction; Chemical vapor deposition; Gallium Indium Phosphides Mixed; Aluminium Gallium Indium Phosphides Mixed

Spanish Descriptors: Laser **semiconductor**; Heterounion doble; Deposito quimico fase vapor; Galio; Aluminio

7/3,K/8 (Item 1 from file: 434)
DIALOG(R)File 434:SciSearch(R) Cited Ref Sci
(c) 1998 Inst for Sci Info. All rts. reserv.

06799242 Genuine Article#: ATT81 No. References: 33
Title: TRANSMISSION ELECTRON-MICROSCOPIC OBSERVATION OF MICRODEFECTS IN ZN+-IMPLANTED GAAS
Author(s): **MORITA E**; KASAHIARA J; KAWADO S
Corporate Source: SONY CORP, RES CTR, 174 FUJITSUKA CHO, HODOGAYA KU/YOKOHAMA/KANAGAWA 240/JAPAN/
Journal: JAPANESE JOURNAL OF APPLIED PHYSICS PART 1-REGULAR PAPERS & SHORT NOTES, 1985, V24, N10, P1274-1281
Language: ENGLISH Document Type: ARTICLE

Author(s): **MORITA E**; KASAHIARA J; KAWADO S
...Research Fronts: POINT DEFECTS FROM PLASTIC DEFORMATION AND DOPING

• EFFECTS IN SILICON, GAAS AND OTHER CRYSTALS AND **SEMICONDUCTORS**))

7/3,K/9 (Item 1 from file: 34)
DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

05388534 Genuine Article#: VV197 No. References: 24
Title: STRUCTURAL-CHANGE OF SELENIUM-TREATED GAAS(001) SURFACE OBSERVED BY STM
Author(s): HAGA Y; MIWA S; **MORITA E**
Corporate Source: SONY CORP,RES CTR,174 FUJITSUKA CHO/YOKOHAMA/KANAGAWA 240/JAPAN/
Journal: APPLIED SURFACE SCIENCE, 1996, V107, NOV (NOV), P58-62
ISSN: 0169-4332
Language: ENGLISH Document Type: ARTICLE (Abstract Available) X

Author(s): HAGA Y; MIWA S; **MORITA E**
Research Fronts: 94-3730 003 (INP SURFACE DURING HYDROGEN PLASMA TREATMENT; III-V COMPOUND **SEMICONDUCTORS** FOR ELECTRONIC PASSIVATION; CRYSTALLINE SILICON; QUANTUM DIFFUSION OF MUONIUM) 94-2555 002 (SURFACE RECONSTRUCTIONS; MOLECULAR-BEAM EPITAXY; MBE-GROWN COMPOUND **SEMICONDUCTORS**) X

7/3,K/10 (Item 2 from file: 34)
DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

04643214 Genuine Article#: BE88Y No. References: 19
Title: STRUCTURAL STUDY OF DEGRADED II-VI BLUE-LIGHT EMITTERS
Author(s): TOMIYA S; UKITA M; OKUYAMA H; NAKANO K; ITOH S; ISHIBASHI A; **MORITA E**; IKEDA M
Corporate Source: SONY CORP,RES CTR,HODOGAYA KU,174 FUJITSUKA CHO/YOKOHAMA/KANAGAWA 240/JAPAN/
Journal: MATERIALS SCIENCE FORUM, 1995, V196-, P1109-1116
ISSN: 0255-5476
Language: ENGLISH Document Type: ARTICLE (Abstract Available) X

Author(s): TOMIYA S; UKITA M; OKUYAMA H; NAKANO K; ITOH S; ISHIBASHI A; **MORITA E**; IKEDA M
...Research Fronts: HIGH-POWER QUANTUM-WELL LASERS; ROD-LIKE DEFECT FORMATION IN SILICON; DIAMOND CUBIC-CRYSTALS; COMPOUND **SEMICONDUCTORS**; THERMAL RUNAWAY; MIRROR TEMPERATURE) 94-6220 001 (METALORGANIC VAPOR-PHASE EPITAXY OF ZNSE; (100) GAAS; DEEP TRAPPING CENTERS; II-VI **SEMICONDUCTORS**) X

7/3,K/11 (Item 3 from file: 34)
DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

04577831 Genuine Article#: TU672 No. References: 21
Title: STRUCTURAL STUDY OF DEGRADED ZNMGSSE BLUE-LIGHT EMITTERS
Author(s): NAKANO K; TOMIYA S; UKITA M; YOSHIDA H; ITOH S; **MORITA E**; IKEDA M; ISHIBASHI A
Corporate Source: SONY CORP,RES CTR,HODOGAYA KU,174 FUJITSUKA CHO/YOKOHAMA/KANAGAWA 240/JAPAN/
Journal: JOURNAL OF ELECTRONIC MATERIALS, 1996, V25, N2 (FEB), P213-216
ISSN: 0361-5235
Language: ENGLISH Document Type: ARTICLE (Abstract Available) X

Author(s): NAKANO K; TOMIYA S; UKITA M; YOSHIDA H; ITOH S; **MORITA E**; IKEDA M; ISHIBASHI A
Research Fronts: 94-2770 003 (MOLECULAR-BEAM EPITAXY; NITROGEN-DOPED ZNSE; BLUE-GREEN II-VI **SEMICONDUCTOR**-LASERS; P-TYPE ZNTE)

- 94-2257 001 (HIGH-POWER QUANTUM-WELL LASERS; ROD-LIKE DEFECT FORMATION IN SILICON; DIAMOND CUBIC-CRYSTALS; COMPOUND **SEMICONDUCTORS**; THERMAL RUNAWAY; MIRROR TEMPERATURE)
- 94-6220 001 (METALORGANIC VAPOR-PHASE EPITAXY OF ZNSE; (100) GAAS; DEEP TRAPPING CENTERS; II-VI **SEMICONDUCTORS**)

7/3,K/12 (Item 4 from file: 34)

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

00931122 Genuine Article#: FG418 No. References: 10

Title: MOCVD GROWTH OF ALGAINP ON A (111)B GAAS SUBSTRATE AND ITS APPLICATION TO VISIBLE LASERS

Author(s): IKEDA M; **MORITA E**; TODA A; YAMAMOTO T; KANEKO K
Corporate Source: SONY CORP, RES CTR, 174 FUJITSUKA CHO, HODOGAYA
KU/YOKOHAMA/KANAGAWA 240/JAPAN/

X

Journal: INSTITUTE OF PHYSICS CONFERENCE SERIES, 1989, N96, P83-88

Language: ENGLISH Document Type: ARTICLE (Abstract Available)

Author(s): IKEDA M; **MORITA E**; TODA A; YAMAMOTO T; KANEKO K
Research Fronts: 89-2212 003 (MOLECULAR-BEAM EPITAXY; METALORGANIC
CHEMICAL VAPOR-DEPOSITION; (110) GAAS SUBSTRATES; ORDERED
SEMICONDUCTORS; BAND-GAP ENERGY)

7/3,K/13 (Item 5 from file: 34)

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

00607060 Genuine Article#: EF126 No. References: 17

Title: EPITAXIAL-GROWTH OF GAINP ON (111)A AND (111)B SURFACES BY METALORGANIC CHEMICAL VAPOR-DEPOSITION

X

Author(s): **MORITA E**; IKEDA M; INOUE M; KANEKO K
Corporate Source: SONY CORP, RES CTR, 174 FUJITSUKA CHO, HODOGAYA
KU/YOKOHAMA/KANAGAWA 240/JAPAN/

Journal: JOURNAL OF CRYSTAL GROWTH, 1990, V106, N2-3, P197-207

Language: ENGLISH Document Type: ARTICLE

Author(s): **MORITA E**; IKEDA M; INOUE M; KANEKO K

Research Fronts: 88-1281 002 (**SEMICONDUCTOR** ALLOYS; ORGANOMETALLIC
VAPOR-PHASE EPITAXY; ABINITIO MOLECULAR-DYNAMICS CALCULATIONS;
ELECTRONIC-PROPERTIES OF AMORPHOUS-SILICON)

88...

7/3,K/14 (Item 1 from file: 94)

DIALOG(R)File 94:JICST-EPlus
(c)2000 Japan Science and Tech Corp(JST). All rts. reserv.

03371353 JICST ACCESSION NUMBER: 97A0751011 FILE SEGMENT: JICST-E
Characterization of Thin Bonded Silicon-on-Insulator Structures by the

X

Microwave Photoconductivity Decay Method.

ICHIMURA M (1); MAKINO T (1); ASAKURA H (1); USAMI A (1); ARAI E (1);
MORITA E (2)

(1) Nagoya Inst. Technol., Nagoya, JPN; (2) Mitsubishi Materials Silicon
Co., Ltd., Noda, JPN

Jpn J Appl Phys Part 2, 1997, VOL.36, NO.7A, PAGE.L839-L841, FIG.5, REF.7
JOURNAL NUMBER: F0599BAD ISSN NO: 0021-4922

UNIVERSAL DECIMAL CLASSIFICATION: 621.382 MIS 621.382.002.2

LANGUAGE: English COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Short Communication

MEDIA TYPE: Printed Publication

; **MORITA E** (2)

...DESCRIPTORS: **semiconductor** thin film
...BROADER DESCRIPTORS: **semiconductor**;

7/3,K/15 (Item 2 from file: 94)
DIALOG(R)File 94:JICST-Eplus
(c)2000 Japan Science and Tech Corp(JST). All rts. reserv.

03121819 JICST ACCESSION NUMBER: 97A0320280 FILE SEGMENT: JICST-E
Contactless Estimation of the Surface Recombination Velocity at High-Low Junction Surfaces Fabricated by the Ion-Implantation Technique.
MAKINO T (1); ICHIMURA M (1); YOSHIDA H (1); USAMI A (1); **MORITA E** (2)
(1) Nagoya Inst. Technol, Nagoya, JPN; (2) Mitsubishi Materials Silicon Co., Ltd., Noda, JPN
Jpn J Appl Phys Part 1, 1997, VOL.36,NO.2, PAGE.601-604, FIG.9, REF.11
JOURNAL NUMBER: G0520BAE ISSN NO: 0021-4922
UNIVERSAL DECIMAL CLASSIFICATION: 621.382.23+
LANGUAGE: English COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Original paper
MEDIA TYPE: Printed Publication

; **MORITA E** (2)
...DESCRIPTORS: **semiconductor**;
...BROADER DESCRIPTORS: **semiconductor** junction

7/3,K/16 (Item 3 from file: 94)
DIALOG(R)File 94:JICST-Eplus
(c)2000 Japan Science and Tech Corp(JST). All rts. reserv.

02358902 JICST ACCESSION NUMBER: 95A0289775 FILE SEGMENT: JICST-E
Effect of SC1 Process on Silicon Surface Microroughness and Oxide Breakdown Characteristics.
AKIYAMA K (1); NAITO N (1); NAGAMORI M (1); SASSA K (1); KOYA H (2);
MORITA E (2); SUGA H (2)
(1) Mitsubishi Meterials Corp., Saitama, JPN; (2) Mitsubishi Meterials Silicon Corp., Chiba, JPN
Jpn J Appl Phys Part 2, 1995, VOL.34,NO.2A, PAGE.L153-L155, FIG.5, REF.6
JOURNAL NUMBER: F0599BAD ISSN NO: 0021-4922
UNIVERSAL DECIMAL CLASSIFICATION: 539.211:621.315.592 621.382.002.2
LANGUAGE: English COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Short Communication
MEDIA TYPE: Printed Publication

; KOYA H (2); **MORITA E** (2); SUGA H (2)
...DESCRIPTORS: **semiconductor**;

7/3,K/17 (Item 4 from file: 94)
DIALOG(R)File 94:JICST-Eplus
(c)2000 Japan Science and Tech Corp(JST). All rts. reserv.

01244746 JICST ACCESSION NUMBER: 91A0378647 FILE SEGMENT: JICST-E
F6631 solid state disk: High-speed virtual disk unit.
SUGIURA H (1); **MORITA E** (1); NAGASAWA S (1)
(1) Fujitsu Ltd., Kawasaki, JPN
Fujitsu Sci Tech J, 1991, VOL.26,NO.4, PAGE.296-305, FIG.9, TBL.3, REF.2
JOURNAL NUMBER: S0076AAR ISSN NO: 0016-2523 CODEN: FUSTA
UNIVERSAL DECIMAL CLASSIFICATION: 681.32.07 681.327
LANGUAGE: English COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Commentary
MEDIA TYPE: Printed Publication

SUGIURA H (1); **MORITA E** (1); NAGASAWA S (1)
...DESCRIPTORS: **semiconductor** memory

7/3,K/18 (Item 5 from file: 94)

DIALOG(R)File 94:JICST-Eplus

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01210024 JICST ACCESSION NUMBER: 91A0200635 FILE SEGMENT: JICST-E

Special issue: Fujitsu file devices. F6631 solid state disk.

SUGIURA HAJIME (1); **MORITA ETSUO** (1); NAGASAWA SOICHIRO (1)

(1) Fujitsu Ltd.

Fujitsu, 1991, VOL.42,NO.1, PAGE.25-33, FIG.9, TBL.3, REF.2

JOURNAL NUMBER: F0397AAQ ISSN NO: 0016-2515 CODEN: FUJTA

UNIVERSAL DECIMAL CLASSIFICATION: 681.327

LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Commentary

MEDIA TYPE: Printed Publication

SUGIURA HAJIME (1); **MORITA ETSUO** (1); NAGASAWA SOICHIRO (1)

DESCRIPTORS: **semiconductor** memory...

7/3,K/19 (Item 6 from file: 94)

DIALOG(R)File 94:JICST-Eplus

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01184059 JICST ACCESSION NUMBER: 91A0125992 FILE SEGMENT: JICST-E

Crystal-originated singularities on Si wafer surface after SC1 cleaning.

RYUTA J (1); **MORITA E** (1); SHIMANUKI Y (1); TANAKA T (2)

(1) Mitsubishi Metal Corp., Saitama; (2) Japan Silicon Co., Ltd., Chiba

Jpn J Appl Phys Part 2, 1990, VOL.29,NO.11, PAGE.L1947-L1949, FIG.6, REF.2

JOURNAL NUMBER: F0599BAD ISSN NO: 0021-4922

UNIVERSAL DECIMAL CLASSIFICATION: 53.084.8

LANGUAGE: English COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Short Communication

MEDIA TYPE: Printed Publication

RYUTA J (1); **MORITA E** (1); SHIMANUKI Y (1)

...DESCRIPTORS: **semiconductor**;

?

8/3,K/1 (Item 1 from file: 144)

DIALOG(R)File 144:Pascal

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13767514 PASCAL No.: 98-0480026

Minority carrier diffusion length in GaN and ZnSe

Nitride semiconductors 1997

MIYAJIMA T; OZAWA M; ASATSUMA T; **KAWAI H**; IKEDA M

HIRAMATSU K, ed; KISHINO K, ed; NAKAMURA S, ed; AMANO H, ed

Research Center, Sony Corporation, 174 Fujitsuka-cho, Hodogaya-ku, Yokohama 240, Japan

Mie University, Japan; Sophia University, Japan; Nichia Chemical Industries, Japan; Meijo University, Japan

The Japan Society of Applied Physics, Japan.

ICNS'97 International Conference on Nitride Semiconductors, 2 (Tokushima JPN) 1997-10-27

Journal: Journal of crystal growth, 1998, 189-90 768-772

Language: English

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MIYAJIMA T; OZAWA M; ASATSUMA T; **KAWAI H**; IKEDA M

... m, which is comparable to that of ZnSe. The threading dislocation density in GaN on **sapphire**, however, is several orders larger than that in ZnSe on GaAs. Therefore, a comparison with ZnSe shows that threading dislocations in GaN on **sapphire** do not act as efficient trap centers for minority carriers.

8/3,K/2 (Item 2 from file: 144)

DIALOG(R)File 144:Pascal

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13708328 PASCAL No.: 98-0399246

Room-temperature continuous-wave operation of GaInN/GaN multiquantum well laser diode

KOBAYASHI T; NAKAMURA F; NAGANUMA K; TOJOY T; NAKAJIMA H; ASATSUMA T;

KAWAI H; IKEDA M

Sony Corp, Yokohama, Japan

Journal: Electronics Letters, 1998, 34 (15) 1494-1495

Language: English

KOBAYASHI T; NAKAMURA F; NAGANUMA K; TOJOY T; NAKAJIMA H; ASATSUMA T; **KAWAI H**; IKEDA M

... MOCVD) using a horizontal reactor. The laser structure was grown on a (0001) c-plane **sapphire** substrate. A 1 mm long cavity with a 4 mu m wide ridge stripe was...

...English Descriptors: Threshold current density; Experiments; Continuous wave lasers; Semiconducting gallium compounds; Nitrides; Metallorganic chemical vapor deposition; **Sapphire**; Stimulated emission; Current density; Quantum well lasers

8/3,K/3 (Item 1 from file: 94)

DIALOG(R)File 94:JICST-EPlus

(c)2000 Japan Science and Tech Corp(JST). All rts. reserv.

03470712 JICST ACCESSION NUMBER: 98A0254741 FILE SEGMENT: JICST-E

An AlN/GaN Insulated Gate Heterostructure Field Effect Transistor; IG-HFET Simulations and Prototype Device Fabrication.

KAWAI HIROJI (1); HARA MASAKI (1); NAKAMURA FUMIHIKO (1); IMANAGA SHUNJI (1)

(1) Sony Corp., Cent. Res. Lab.

Densi Joho Tsushin Gakkai Gijutsu Kenkyu Hokoku(IEIC Technical Report (Institute of Electronics, Information and Communication Engineers),

1998, VOL.97, NO.475(ED97 188-195), PAGE.21-26, FIG.7, TBL.2, REF.15
JOURNAL NUMBER: S0532BBG
UNIVERSAL DECIMAL CLASSIFICATION: 621.382.3
LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Original paper
MEDIA TYPE: Printed Publication

KAWAI HIROJI (1); HARA MASAKI (1); NAKAMURA FUMIHIKO (1); IMANAGA
SHUNJI (1)

...ABSTRACT: mm. The structure was the stack of AlN(4nm)/n+GaN(15nm)/AlGaN
layers on **sapphire** substrate, which were grown sequentially by
MOCVD. The device operated with gate voltage up to...

?

X

```

show files;ds;t 13/3,k/all
File 2:INSPEC 1969-2000/Jun W3
    (c) 2000 Institution of Electrical Engineers
File 8:Ei Compendex(R) 1970-2000/Jul W1
    (c) 2000 Engineering Info. Inc.
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File 238:Abs. in New Tech & Eng. 1981-2000/Jul
    (c) 2000 Reed-Elsevier (UK) Ltd.
File 65:Inside Conferences 1993-2000/Jul W3
    (c) 2000 BLDSC all rts. reserv.

```

Set	Items	Description
S1	291	AU="MORITA E" OR AU="MORITA ETSUO"
S2	2103	AU="KAWAI H"
S3	18	AU="KAWAI HIROJI"
S4	0	S1 AND SAPPHIRE?
S5	23	S1 AND (SEMICONDUCTOR? OR SEMI()CONDUCT?)
S6	5	(S2 OR S3) AND SAPPHIRE?
S7	19	RD S5 (unique items)
S8	3	RD S6 (unique items)
S9	88	(S2 OR S3) AND (SEMICONDUCT? OR SEMI()CONDUCT?)
S10	19	S9 AND (LIGHT? OR LASER?)
S11	17	RD (unique items)
S12	19	S8 OR S11
S13	19	RD (unique items)

>>>KWIC option is not available in file(s): 14, 77

```

13/3,K/1      (Item 1 from file: 144)
DIALOG(R)File 144:Pascal
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```

14027013 PASCAL No.: 99-0215637

Magnetic response of Cd SUB 0 SUB . SUB 6 SUB 3 Mn SUB 0 SUB . SUB 3 SUB

7 Te under illumination: Dynamic behavior of spin glass with step-like heating and cooling

KAWAI H; SATO T

Department of Applied Physics and Physico-Informatics, Faculty of Science and Technology, Keio University, 3-14-1 Hiyoshi, Kohoku-ku, Yokohama-shi, Kanagawa, Japan

Journal: Journal of applied physics, 1999-05-15, 85 (10) 7310-7315

Language: English

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KAWAI H; SATO T

The magnetic behavior of a typical diluted magnetic **semiconductor** Cd SUB 0 SUB . SUB 6 SUB 3 Mn SUB 0 SUB . SUB 3 SUB 7 Te was investigated under the unpolarized **light** illumination in a magnetic field. Both the zero field cooled (ZFC) and field cooled (FC...).

English Descriptors: Experimental study; Semimagnetic **semiconductors**; Cadmium compounds; Manganese compounds; Spin dynamics; Spin glasses; Magnetization

French Descriptors: 7540G; 7550L; 7550P; 7560E; Etude experimentale; **Semiconducteur** semimagnetique; Cadmium compose; Manganese compose; Dynamique spin; Verre spin; Aimantation

13/3,K/2 (Item 2 from file: 144)

DIALOG(R)File 144:Pascal

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13772732 PASCAL No.: 98-0485739

Room-temperature pulsed operation of a GaInN multiple-quantum-well
laser diode with optimized well number
Nitride **semiconductors** 1997
NAKAMURA F; KOBAYASHI T; ASATSUMA T; FUNATO K; YANASHIMA K; HASHIMOTO S; NAGANUMA K; TOMIOKA S; MIYAJIMA T; MORITA E; **KAWAI H**; IKEDA M
HIRAMATSU K, ed; KISHINO K, ed; NAKAMURA S, ed; AMANO H, ed
Research Center, Sony Corporation, 174 Fujitsuka-cho, Hodogaya-ku, Yokohama 240, Japan

Mie University, Japan; Sophia University, Japan; Nichia Chemical Industries, Japan; Meijo University, Japan
The Japan Society of Applied Physics, Japan.
ICNS'97 International Conference on Nitride Semiconductors, 2 (Tokushima JPN) 1997-10-27

Journal: Journal of crystal growth, 1998, 189-90 841-845

Language: English

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Room-temperature pulsed operation of a GaInN multiple-quantum-well
laser diode with optimized well number
Nitride **semiconductors** 1997
...T; FUNATO K; YANASHIMA K; HASHIMOTO S; NAGANUMA K; TOMIOKA S; MIYAJIMA T; MORITA E; **KAWAI H**; IKEDA M
... of the optical pumping threshold power for stimulated emission of GaInN multiple quantum-well (MQW) **laser** structures was investigated. The pumping threshold power for a three GaInN MQW sample was found...

... SUP 2 at room temperature. The room-temperature pulsed operation of a five GaInN MQW **laser** diode (LD), whose number of wells was determined based on the optical pumping experiment, was...

English Descriptors: Injection **laser**; **Semiconductor** **laser**;
Multiple quantum well; Room temperature; III-V compound; Gallium Nitrides
; Binary compound; Indium Nitrides; Ternary...

French Descriptors: **Laser** injection; **Laser** **semiconducteur**;
Puits quantique multiple; Temperature ambiante; Compose III-V; Gallium
Nitrure; Compose binaire; Indium Nitrure; Compose...

Spanish Descriptors: **Laser** inyeccion; **Laser** **semiconductor**; Pozo
cuantico multiple; Temperatura ambiente; Comuesto III-V; Galio Nitruro;
Comuesto binario; Indio Nitruro; Comuesto...

13/3,K/3 (Item 3 from file: 144)

DIALOG(R)File 144:Pascal
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13767514 PASCAL No.: 98-0480026

Minority carrier diffusion length in GaN and ZnSe

Nitride semiconductors 1997

MIYAJIMA T; OZAWA M; ASATSUMA T; **KAWAI H**; IKEDA M
HIRAMATSU K, ed; KISHINO K, ed; NAKAMURA S, ed; AMANO H, ed
Research Center, Sony Corporation, 174 Fujitsuka-cho, Hodogaya-ku,
Yokohama 240, Japan

Mie University, Japan; Sophia University, Japan; Nichia Chemical
Industries, Japan; Meijo University, Japan

The Japan Society of Applied Physics, Japan.

ICNS'97 International Conference on Nitride Semiconductors, 2 (Tokushima
JPN) 1997-10-27

Journal: Journal of crystal growth, 1998, 189-90 768-772

Language: English

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MIYAJIMA T; OZAWA M; ASATSUMA T; **KAWAI H**; IKEDA M
... m, which is comparable to that of ZnSe. The threading dislocation
density in GaN on **sapphire**, however, is several orders larger than that
in ZnSe on GaAs. Therefore, a comparison with ZnSe shows that threading
dislocations in GaN on **sapphire** do not act as efficient trap centers
for minority carriers.

13/3,K/4 (Item 4 from file: 144)

DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

13708328 PASCAL No.: 98-0399246

**Room-temperature continuous-wave operation of GaInN/GaN multiquantum well
laser diode**

KOBAYASHI T; NAKAMURA F; NAGANUMA K; TOJOY T; NAKAJIMA H; ASATSUMA T;
KAWAI H; IKEDA M

Sony Corp, Yokohama, Japan

Journal: Electronics Letters, 1998, 34 (15) 1494-1495

Language: English

**Room-temperature continuous-wave operation of GaInN/GaN multiquantum well
laser diode**

KOBAYASHI T; NAKAMURA F; NAGANUMA K; TOJOY T; NAKAJIMA H; ASATSUMA T;
KAWAI H; IKEDA M

Continuous-wave operation at room temperature was demonstrated in a
GaInN/GaN multiquantum well (MQW) **laser** grown by metal organic
chemical vapour deposition (MOCVD) using a horizontal reactor. The
laser structure was grown on a (0001) c-plane **sapphire** substrate. A
1 mm long cavity with a 4 mu m wide ridge stripe was...

English Descriptors: Gallium indium nitride; Gallium nitride; Threshold
current density; Experiments; Continuous wave **lasers**;
Semiconducting gallium compounds; Nitrides; Metallorganic chemical
vapor deposition; **Sapphire**; Stimulated emission; Current density;
Quantum well **lasers**

French Descriptors: Experience; **Laser** continu; Compose
semiconducteur gallium; Nitrure; Depot chimique phase vapeur compose
organometallique; Saphir; Emission stimulee; Densite courant; **Laser**
puits quantique

13/3,K/5 (Item 5 from file: 144)
DIALOG(R)File 144:Pascal
(c) 2000 INIST/CNRS. All rts. reserv.

13631588 PASCAL No.: 98-0337768
Room-temperature pulsed operation of a GaInN multiple-quantum-well
laser diode
NAKAMURA F; KOBAYASHI T; TOJO T; ASATSUMA T; NAGANUMA K; **KAWAI H**;
IKEDA M
Sony Corp, Yokohama, Japan
Journal: Electronics Letters, 1998, 34 (11) 1105-1107
Language: English

Room-temperature pulsed operation of a GaInN multiple-quantum-well
laser diode

NAKAMURA F; KOBAYASHI T; TOJO T; ASATSUMA T; NAGANUMA K; **KAWAI H**;
IKEDA M

The room-temperature pulsed operation of a five GaInN multiple-quantum-well (MQW) **laser** diode (LD) is reported. The lowest threshold current density was 9.5 kA/cm². The highest external differential quantum efficiency was 49% for a 1 mm long cavity. The **laser** wavelength was 417.5 nm with a full width at half maximum (FWHM) of less...

... was 185 K. Pulsed operation of the LD up to 80 Degree C was demonstrated. **Laser** operation was confirmed with a duty cycle up to 10%.

English Descriptors: Room temperature pulsed operation; Theory;
Semiconducting gallium compounds; Current density; Quantum efficiency
; Cavity resonators; Quantum well **lasers**; Experiments

French Descriptors: Theorie; Compose **semiconducteur** gallium; Densite courant; Efficacite quantique; Resonateur cavite; **Laser** puits quantique; Experience

13/3,K/6 (Item 6 from file: 144)
DIALOG(R)File 144:Pascal
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05872788 PASCAL No.: 84-0374392
High Al-content visible (AlGa)As multiple quantum well heterostructure
lasers grown by metalorganic chemical vapor deposition
KAWAI H; MATSUDA O; KANEKO K
Sony res. center, Yokohama 240, Japan
Journal: Japanese Journal of applied Physics, 1983, 22 (11 part 2)
L727-L729
Language: English

High Al-content visible (AlGa)As multiple quantum well heterostructure
lasers grown by metalorganic chemical vapor deposition
KAWAI H; MATSUDA O; KANEKO K

English Descriptors: Epitaxy; Chemical vapor deposition; Organometallic compound; **Semiconductor** **laser**; Aluminium Gallium Arsenides Mixed; Crystal growth; Visible radiation; Heterojunction

French Descriptors: Epitaxie; Depot chimique phase vapeur; Compose organometallique; **Laser** **semiconducteur**; Aluminium Gallium

Arseniure Mixte; Croissance cristalline; Rayonnement visible;
Heterojonction; Puits quantique multiple

13/3,K/7 (Item 7 from file: 144)
DIALOG(R)File 144:Pascal
(c). 2000 INIST/CNRS. All rts. reserv.

05525682 PASCAL No.: 84-0025789

Effect of an active layer thickness on lateral and longitudinal modes of a gain guiding **laser with a tapered stripe structure**

MAMINE T; **KAWAI H**

SONY corp., Atsugi-shi 243, Japan

Journal: Applied Physics Letters, 1983, 43 (3) 235-237

Language: English

Effect of an active layer thickness on lateral and longitudinal modes of a gain guiding **laser with a tapered stripe structure**

MAMINE T; **KAWAI H**

L'etude de cet effet montre que pour de tels **lasers** ayant des couches actives de 0,10 et 0,15 μ m d'epaisseur, les...

English Descriptors: **Semiconductor** **laser**

French Descriptors: **Laser** **semiconducteur**; Mode longitudinal;
Laser guidage gain

13/3,K/8 (Item 1 from file: 434)

DIALOG(R)File 434:SciSearch(R) Cited Ref Sci
(c) 1998 Inst for Sci Info. All rts. reserv.

07630328 Genuine Article#: E6861 No. References: 8

**Title: SINGLE AND COUPLED DOUBLE-WELL GAAS/ALGAAS AND ENERGY-DEPENDENT
LIGHT-HOLE MASS**

Author(s): WATANABE N; **KAWAI H**

Corporate Source: SONY CORP, RES CTR, 174 FUJITSUKACHO, HODOGAYA
KU/YOKOHAMA/KANAGAWA 240/JAPAN/

Journal: JOURNAL OF APPLIED PHYSICS, 1986, V60, N10, P3696-3698

Language: ENGLISH Document Type: ARTICLE

**Title: SINGLE AND COUPLED DOUBLE-WELL GAAS/ALGAAS AND ENERGY-DEPENDENT
LIGHT-HOLE MASS**

Author(s): WATANABE N; **KAWAI H**

Research Fronts: 86-0923 002 (BAND OFFSETS IN **SEMICONDUCTOR** QUANTUM
WELLS; MODULATION-DOPED HETEROSTRUCTURES; HOT CARRIERS; MOBILITY OF THE
TWO-DIMENSIONAL ELECTRON-GAS)

13/3,K/9 (Item 1 from file: 34)

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

07663627 Genuine Article#: 193KT No. References: 18

**Title: Magnetic response of Cd_{0.63}Mn_{0.37}Te under illumination: Dynamic
behavior of spin glass with step-like heating and cooling**

Author(s): **Kawai H (REPRINT) **; Sato T

Corporate Source: KEIO UNIV, FAC SCI & TECHNOL, DEPT APPL PHYS &
PHYSICOINFORMAT, KOHOKU KU, 3-14-1 HIYO/YOKOHAMA/KANAGAWA 223/JAPAN/
(REPRINT)

Journal: JOURNAL OF APPLIED PHYSICS, 1999, V85, N10 (MAY 15), P7310-7315
ISSN: 0021-8979 Publication date: 19990515

Publisher: AMER INST PHYSICS, CIRCULATION FULFILLMENT DIV, 500 SUNNYSIDE
BLVD, WOODBURY, NY 11797-2999

Language: English Document Type: ARTICLE (ABSTRACT AVAILABLE)

Author(s): **Kawai H (REPRINT) **; Sato T

Abstract: The magnetic behavior of a typical diluted magnetic
semiconductor Cd_{0.63}Mn_{0.37}Te was investigated under the unpolarized
light illumination in a magnetic field. Both the zero field cooled
(ZFC) and field cooled (FC...
...Identifiers--CD1-XMNXTE; CD1-X-YMNXFYSTE; SUSCEPTIBILITY;
SEMICONDUCTOR

13/3,K/10 (Item 2 from file: 34)

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

07084545 Genuine Article#: 122HL No. References: 5

Title: Electron cyclotron resonance (ECR) sputtered antireflection coatings
on **laser** facets for optical memory applications

Author(s): Kim YJ (REPRINT) ; Tateno R; Ikura T; Matsuda K; **Kawai H**;
Suzuki M; Goto K

Corporate Source: TOKAI UNIV,DEPT INFORMAT & COMMUN TECHNOL/SHIZUOKA
41003//JAPAN/ (REPRINT); SAMSUNG ELECTROMECH CO LTD,CTR RES & DEV/SUWON
442743/KYUNGKI DO/SOUTH KOREA/; ASAHI TECH LAB CO LTD,DIV OA
BUSINESS/HAMAMATSU/SHIZUOKA 434/JAPAN/

Journal: JAPANESE JOURNAL OF APPLIED PHYSICS PART 1-REGULAR PAPERS SHORT
NOTES & REVIEW PAPERS, 1998, V37, N4B (APR), P2201-2202

ISSN: 0021-4922 Publication date: 19980400

Publisher: JAPAN J APPLIED PHYSICS, DAINI TOYOKAIJI BLDG 24-8 SHINBASHI
4-CHOME, MINATO-KU TOKYO 105, JAPAN

Language: English Document Type: ARTICLE (ABSTRACT AVAILABLE)

Title: Electron cyclotron resonance (ECR) sputtered antireflection coatings
on **laser** facets for optical memory applications

Author(s): Kim YJ (REPRINT) ; Tateno R; Ikura T; Matsuda K; **Kawai H**;
Suzuki M; Goto K

Abstract: Antireflection (AR) layer coated **semiconductor**/**laser**
diodes may have many applications. particularly as external cavity
diodes for optical memory heads. The...

...gas flow rate. the RF and ECR power, and the deposition time. AR seated
AlGaAs **laser** diodes do not show a sharp threshold in the **light**
output-current characteristic curve and have good potential for
application in the lensless optical floppy...

13/3,K/11 (Item 3 from file: 34)

DIALOG(R)File 34:SciSearch(R) Cited Ref Sci
(c) 2000 Inst for Sci Info. All rts. reserv.

05638451 Genuine Article#: WM648 No. References: 4

Title: Concentration dependence of photo-induced magnetization in diluted
magnetic **semiconductor** Cd_{1-x}Mn_xTe

Author(s): Yamaguchi Y (REPRINT) ; **Kawai H**; Sato T

Corporate Source: KEIO UNIV,FAC SCI & TECHNOL, DEPT INSTRUMENTAT ENGN,
KOHOKU KU, 3-14-1 HIYOSHI/YOKOHAMA/KANAGAWA 223/JAPAN/ (REPRINT)

Journal: ACTA PHYSICA POLONICA A, 1997, V91, N2 (FEB), P479-482

ISSN: 0587-4246 Publication date: 19970200

Publisher: POLISH ACAD SCIENCES INST PHYSICS, AL LOTNIKOW 32-46, 02-668
WARSAW, POLAND

Language: English Document Type: ARTICLE (ABSTRACT AVAILABLE)

Title: Concentration dependence of photo-induced magnetization in diluted
magnetic **semiconductor** Cd_{1-x}Mn_xTe

Author(s): Yamaguchi Y (REPRINT) ; **Kawai H**; Sato T

...Abstract: Delta M(photo) was observed in Cd_{1-x}Mn_xTe (0.25 < x < 0.42)
under unpolarized **light** illumination whose photon energy is smaller
than the band gap of the sample. The photo...

13/3,K/12 (Item 1 from file: 103)

DIALOG(R)File 103:Energy SciTec

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04489683 AIX-30-032159; EDB-99-070362

Title: Concentration dependence of photo-induced magnetization in diluted magnetic **semiconductor** Cd_{1-x}Mn_xTe

Author(s): Yamaguchi, Y.; **Kawai, H.**; Sato, T. (Department of Instrumentation Engineering, Faculty of Science and Technology, Keio University, Kanagawa (Japan)

Corporate Source: Institute of Molecular Physics, Polish Academy of Sciences, Poznan (Poland) Institute of Physics, A. Mickiewicz University, Poznan (Poland) Polish Physical Society, Warsaw (Poland)

Conference Title: European Conference 'Physics of Magnetism 96'

Conference Location: Poznan (Poland) **Conference Date:** 24-28 Jun 1996

Source: Acta Physica Polonica, Series A v 91:2. **Coden:** ATPLB6 **ISSN:** 0587-4246

Publication Date: 1997 **p** 479-482

Report Number(s): CONF-9606425--

Language: English

Title: Concentration dependence of photo-induced magnetization in diluted magnetic **semiconductor** Cd_{1-x}Mn_xTe

...**Author(s):** **Kawai, H.**

...**Abstract:** Cd_{1-x}Mn_xTe (0.25 < x < 0.42) under unpolarized **light** illumination whose photon energy is smaller than the band gap of the sample. The photo...

...**Descriptors:** MAGNETIC **SEMICONDUCTORS**;

...**Broader Terms:** **SEMICONDUCTOR** MATERIALS

13/3,K/13 (Item 2 from file: 103)

DIALOG(R)File 103:Energy SciTec

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03665047 NEDO-94-910166; EDB-94-081013

Title: Reduced absorption coefficients of the 4p-4s line of K and the 6p-6s line of Cs under the conditions of closed-cycle MHD working gases

Original Title: Closed cycle MHD no unten jokenka deno kalium genshi 4p-4s sen'i to seshiumu genshi 6p-6s sen'i no kansan kyushu keisu no kettei

Author(s): **Kawai, H.**; Yoshikawa, K.; Shiota, S. (Tokyo Institute of Technology, Tokyo (Japan)); Hasegawa, Y. (Mechanical Engineering Laboratory, Tsukuba (Japan)); Morita, K. (Nissan Motor Co. Ltd., Tokyo (Japan)

Source: Nippon Kikai Gakkai Ronbunshu. B Hen (Transactions of the Japan Society of Mechanical Engineers. Part B) (Japan) v 59:568. **Coden:** NKGBDD **ISSN:** 0387-5016

Publication Date: 25 Dec 1993 **p** 164-170

Language: Japanese

Author(s): **Kawai, H.**...

...**Abstract:** the profile of the absorption coefficient through measurements of an emission spectrum and transmissivity of **semiconductor** **laser**. Since the reduced absorption coefficient was unaffected by working gas temperature, the fraction of seed...

...**Descriptors:** **SEMICONDUCTOR** **LASERS**

...**Broader Terms:** **LASERS**; ...

...**SEMICONDUCTOR** DEVICES...

...SOLID STATE **LASERS**;

13/3,K/14 (Item 3 from file: 103)

DIALOG(R)File 103:Energy SciTec

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01586578 FRG-84-05433; EDB-85-093357

Title: Improvement in the efficiency of amorphous silicon solar cells utilizing the optical confinement effect by means of a TiO₂/sub 2//Ag/SUS back-surface reflector

Author(s): Fujimoto, K.; **Kawai, H.**; Okamoto, H.; Hamakawa, J

Source: Sol. Cells (Switzerland) v 11:4. Coden: SOCLD

Publication Date: May 1984 p 357-366

Language: English

...**Author(s):** **Kawai, H**

...**Abstract:** SUS represents high grade mirror etched stainless steel) highly reflective semitextured substrate acting as a **light** scatterer was developed. Inverted-type a-Si solar cells fabricated on this substrate exhibit a...

...**Descriptors:** **SEMICONDUCTOR** MATERIALS

13/3,K/15 (Item 1 from file: 94)

DIALOG(R)File 94:JICST-EPlus

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03620112 JICST ACCESSION NUMBER: 98A0605216 FILE SEGMENT: JICST-E

Electron Cyclotron Resonance (ECR) Sputtered Antireflection Coatings on **Laser Facets for Optical Memory Applications.**

TATENO R (1); IKURA T (1); MATSUDA K (1); **KAWAI H** (1); GOTO K (1); KIM Y-J (2); SUZUKI M (3)

(1) Tokai Univ., Shizuoka, JPN; (2) Samsung Electro-Mechanics Co., Ltd., Kyungki-Do, KOR; (3) Asahi Technical Lab. Co., Ltd., Hamamatsu, JPN

Jpn J Appl Phys Part 1, 1998, VOL.37, NO.4B, PAGE.2201-2202, FIG.4, REF.5

JOURNAL NUMBER: G0520BAE ISSN NO: 0021-4922

UNIVERSAL DECIMAL CLASSIFICATION: 621.375.826:621.315.592 681.7

621.3:681.327.1

LANGUAGE: English COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Short Communication

MEDIA TYPE: Printed Publication

Electron Cyclotron Resonance (ECR) Sputtered Antireflection Coatings on **Laser Facets for Optical Memory Applications.**

TATENO R (1); IKURA T (1); MATSUDA K (1); **KAWAI H** (1); GOTO K (1)

ABSTRACT: Antireflection (AR) layer coated **semiconductor** **laser** diodes may have many applications, particularly as external cavity diodes for optical memory heads. The...

...gas flow rate, the RF and ECR power, and the deposition time. AR coated AlGaAs **laser** diodes do not show a sharp threshold in the **light** output-current characteristic curve and have good potential for application in the lensless optical floppy...

DESCRIPTORS: **semiconductor** **laser**; ...

...compound **semiconductor**; ...

...**laser** output

BROADER DESCRIPTORS: **laser**; ...

...**semiconductor**;

13/3,K/16 (Item 2 from file: 94)

DIALOG(R)File 94:JICST-EPlus

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03470712 JICST ACCESSION NUMBER: 98A0254741 FILE SEGMENT: JICST-E

An AlN/GaN Insulated Gate Heterostructure Field Effect Transistor; IG-HFET

Simulations and Prototype Device Fabrication.

KAWAI HIROJI (1); HARA MASAKI (1); NAKAMURA FUMIHIKO (1); IMANAGA SHUNJI (1)

(1) Sony Corp., Cent. Res. Lab.

Denshi Joho Tsushin Gakkai Gijutsu Kenkyu Hokoku (IEIC Technical Report (Institute of Electronics, Information and Communication Engineers), 1998, VOL.97, NO.475(ED97 188-195), PAGE.21-26, FIG.7, TBL.2, REF.15

JOURNAL NUMBER: S0532BBG

UNIVERSAL DECIMAL CLASSIFICATION: 621.382.3

LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Original paper

MEDIA TYPE: Printed Publication

KAWAI HIROJI (1); HARA MASAKI (1); NAKAMURA FUMIHIKO (1); IMANAGA SHUNJI (1)

...ABSTRACT: mm. The structure was the stack of AlN(4nm)/n+GaN(15nm)/AlGaN layers on **sapphire** substrate, which were grown sequentially by MOCVD. The device operated with gate voltage up to...

13/3,K/17 (Item 3 from file: 94)

DIALOG(R)File 94:JICST-EPlus

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03216737 JICST ACCESSION NUMBER: 97A0793393 FILE SEGMENT: JICST-E

A study of stable micro-gap control between optical head and optical disk with application of hydrodynamics.

KAWAI H (1); KOJIMA Y (1); SUZUKI M (1); HASEGAWA Y (1); GOTO K (1)

(1) Tokai Univ., Shizuoka, JPN

J Adv Sci, 1997, VOL.9, NO.1/2, PAGE.130-131, FIG.4, REF.3

JOURNAL NUMBER: L0590AAV ISSN NO: 0915-5651

UNIVERSAL DECIMAL CLASSIFICATION: 681.327

LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Original paper

MEDIA TYPE: Printed Publication

KAWAI H (1); KOJIMA Y (1); SUZUKI M (1); HASEGAWA Y (1); GOTO K (1)

...DESCRIPTORS: **semiconductor** **laser**;

...BROADER DESCRIPTORS: **laser**; ...

...**semiconductor** device

13/3,K/18 (Item 4 from file: 94)

DIALOG(R)File 94:JICST-EPlus

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00207107 JICST ACCESSION NUMBER: 86A0159773 FILE SEGMENT: JICST-E

Analysis of AlGaAs-GaAs heterointerfaces using optical methods.

KAWAI HIROJI (1); KANEKO KUNIO (1)

(1) SONY Corp., CenTral Res. Labs.

Hyomen Kagaku (Journal of the Surface Science Society of Japan), 1985, VOL.6, NO.4, PAGE.280-287, FIG.9, REF.35

JOURNAL NUMBER: F0940BAL ISSN NO: 0388-5321

UNIVERSAL DECIMAL CLASSIFICATION: 539.211:621.315.592 621.382 SS

LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Review article

MEDIA TYPE: Printed Publication

KAWAI HIROJI (1); KANEKO KUNIO (1)

ABSTRACT: Recent progress in analyzing AlGaAs-GaAs **semiconductor** heterointerfaces using optical methods, such as photoluminescent spectroscopy, photo-absorption spectroscopy,

photoluminescence-excitation spectroscopy and **laser**-Raman spectroscopy, is reviewed. Three types of interface disorders are discussed: compositional grading parallel to...

...interface roughness of one monolayer can be detected. Emphasis is put on the potential of **laser**-Raman and picosecond time-resolved spectroscopy to investigate the unique properties of superlattice structures. (author...

~ ' ...DESCRIPTORS: compound **semiconductor**;
...BROADER DESCRIPTORS: **semiconductor**; ...

...**semiconductor** junction

13/3,K/19 (Item 5 from file: 94)

DIALOG(R)File 94:JICST-Eplus

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00017557 JICST ACCESSION NUMBER: 85A0034446 FILE SEGMENT: JICST-E

The - 100 meV photoluminescence peak in n-type $\text{Al}_x\text{Ga}_{1-x}\text{As}$ grown by MOCVD.

SAKAMOTO M (1); OKADA T (1); **KAWAI H** (2); MÓRI Y (2); KANEKO K (2)

(1) Sony Corp., Atsugi-shi; (2) Sony Corp., Yokohama

Jpn J Appl Phys Part 2, 1984, VOL.23,NO.7, PAGE.L461-L463, FIG.4, REF.7

JOURNAL NUMBER: F0599BAD ISSN NO: 0021-4922

UNIVERSAL DECIMAL CLASSIFICATION: 535.376:621.315.592 621.383:535.35

LANGUAGE: English COUNTRY OF PUBLICATION: Japan

DOCUMENT TYPE: Journal

ARTICLE TYPE: Original paper

MEDIA TYPE: Printed Publication

; **KAWAI H** (2); MORI Y (2); KANEKO K (2)

...DESCRIPTORS: N-type **semiconductor**; ...

...**light** emitting diode

...BROADER DESCRIPTORS: extrinsic **semiconductor**; ...

...**semiconductor**; ...

...**semiconductor** device

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05196074 SUPPLIER NUMBER: 55802409
Primers for amplifying an alanine racemase gene fragment to detect *E. coli* strains in foods.
Yokoigawa, K.; Inoue, K.; Okubo, Y.; **Kawai, H.**
Journal of Food Science, 64, 4, 571(5)
July-August, 1999
ISSN: 0022-1147 LANGUAGE: English RECORD TYPE: Abstract

5/3/2 (Item 2 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.
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05120358 SUPPLIER NUMBER: 54829953
Magnetic responses of Cd_{0.63}Mn_{0.37}Te under illumination:
dynamic behavior of spin glass with step-like heating and cooling.
Sato, T.; **Kawai, H.**
Journal of Applied Physics, 85, 10, 7310(6)
May 15, 1999
ISSN: 0021-8979 LANGUAGE: English RECORD TYPE: Abstract

5/3/3 (Item 3 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.
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04869675 SUPPLIER NUMBER: 21015422
Residual strength of aging aircraft with multiple site damage/multiple element damage.
Wang, L.; Chow, W.T.; **Kawai, H.**; Atluri, S.N
AIAA Journal, v36, n5, p840(8)
May, 1998
ISSN: 0001-1452 LANGUAGE: English RECORD TYPE: Abstract

5/3/4 (Item 4 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.
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04754114 SUPPLIER NUMBER: 20637104
Predictions of widespread fatigue damage thresholds in aging aircraft.
Wang, L.; Chow, W.T.; **Kawai, H.**; Atluri, S.N
AIAA Journal, v36, n3, p457(8)
March, 1998
ISSN: 0001-1452 LANGUAGE: English RECORD TYPE: Abstract

5/3/5 (Item 5 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.
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04689965 SUPPLIER NUMBER: 20439043
Novel AlN/GaN insulated gate heterostructure field effect transistor with modulation doping and one-dimensional simulation of charge control.
Imanaga, Syunji; **Kawai, Hiroji**
Journal of Applied Physics, v82, n11, p5843(16)
Dec 1, 1997
ISSN: 0021-8979 LANGUAGE: English RECORD TYPE: Abstract

5/3/6 (Item 6 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.
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04647906 SUPPLIER NUMBER: 20300734
Surface morphology changes in ZnSe-related II-VI epitaxial films grown by molecular beam epitaxy.
Tomoya, S.; Minatoya, R.; Tsukamoto, H.; Itoh, S.; Nakano, K.; **Morita, E.**; Ishibashi, A
Journal of Applied Physics, v82, n6, p2938(6)
Sep 15, 1997
ISSN: 0021-8979 LANGUAGE: English RECORD TYPE: Abstract

5/3/7 (Item 7 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.
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03334662 SUPPLIER NUMBER: 15706445
Study on the turbine vane and blade for a 1500 degrees C-class industrial gas turbine.
Amagasa, S.; Shimomura, K.; Kadokawa, M.; Takeishi, K.; **Kawai, H.**;
Aoki, S.; Aoyama, K
Journal of Engineering for Gas Turbines and Power, v116, n3, p597(8)
July, 1994
ISSN: 0742-4795 LANGUAGE: English RECORD TYPE: Citation

5/3/8 (Item 1 from file: 484)
DIALOG(R)File 484:Periodical Abstracts PlusText
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01759292

Suppression of hyperventilation-induced attacks with infusion of atrial natriuretic peptide in patients with variant angina pectoris

Tanaka, Hidenori; Yasue, Hiroyuki; Yoshimura, Michihiro; **Morita, Etsuo**; et al

American Journal of Cardiology (IACR), v72 n2, p128-133

Jul 15, 1993

ISSN: 0002-9149 JOURNAL CODE: IACR

DOCUMENT TYPE: Feature

LANGUAGE: English RECORD TYPE: Abstract

LENGTH: Long (31+ col inches)

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